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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/790,366	03/01/2004	Christopher F. Lyons	H1596	9354
45305 75	90 12/15/2005		EXAMINER	
RENNER, OTTO, BOISSELLE & SKLAR, LLP (AMDS)			BLUM, DAVID S	
	AVE - 19TH FLOOR OH 44115-2191		ART UNIT PAPER NUMBER	
CLEVELAND,	011 44113 2171		2813	

DATE MAILED: 12/15/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

		<i>_</i>	12
	Application No.	Applicant(s)	
	10/790,366	LYONS ET AL.	
Office Action Summary	Examiner	Art Unit	
	David S. Blum	2813	
The MAILING DATE of this communicatio Period for Reply	n appears on the cover sheet w	ith the correspondence address	
A SHORTENED STATUTORY PERIOD FOR R WHICHEVER IS LONGER, FROM THE MAILIN  - Extensions of time may be available under the provisions of 37 C after SIX (6) MONTHS from the mailing date of this communicatir  - If NO period for reply is specified above, the maximum statutory in the set or extended period for reply will, by Any reply received by the Office later than three months after the earned patent term adjustment. See 37 CFR 1.704(b).	NG DATE OF THIS COMMUNI FR 1.136(a). In no event, however, may a on. period will apply and will expire SIX (6) MON statute, cause the application to become Al	CATION.  reply be timely filed  ITHS from the mailing date of this communical  BANDONED (35 U.S.C. § 133).	
Status			
1) Responsive to communication(s) filed on			
2a) This action is <b>FINAL</b> . 2b) ⊠	This action is non-final.		
3) Since this application is in condition for al	lowance except for formal mat	ers, prosecution as to the merits	is
. closed in accordance with the practice un	der <i>Ex par</i> te Quayle, 1935 C.D	). 11, 453 O.G. 213.	
. · Disposition of Claims			
4)⊠ Claim(s) <u>1-20</u> is/are pending in the applic	ation.		
4a) Of the above claim(s) <u>10-20</u> is/are with			
5) Claim(s) is/are allowed.			
6)⊠ Claim(s) <u>1-9</u> is/are rejected.			
7) Claim(s) is/are objected to.			
8) Claim(s) <u>1-20</u> are subject to restriction an	d/or election requirement.		
Application Papers			
9)☐ The specification is objected to by the Exa	aminer.		
10) The drawing(s) filed on is/are: a)	_	by the Examiner.	
Applicant may not request that any objection t	to the drawing(s) be held in abeya	nce. See 37 CFR 1.85(a).	
Replacement drawing sheet(s) including the c	orrection is required if the drawing	(s) is objected to. See 37 CFR 1.12	1(d).
11)☐ The oath or declaration is objected to by the	he Examiner. Note the attache	d Office Action or form PTO-152.	ı
Priority under 35 U.S.C. § 119			
12) Acknowledgment is made of a claim for fo a) All b) Some * c) None of:	reign priority under 35 U.S.C.	§ 119(a)-(d) or (f).	
1.☐ Certified copies of the priority docu	ments have been received.		
2. Certified copies of the priority docu		application No	
3. Copies of the certified copies of the			
application from the International B	ureau (PCT Rule 17.2(a)).	_	
* See the attached detailed Office action for	a list of the certified copies not	received.	
·			
Attachment(s)			
Notice of References Cited (PTO-892)		Summary (PTO-413)	
<ul> <li>Notice of Draftsperson's Patent Drawing Review (PTO-94</li> <li>Information Disclosure Statement(s) (PTO-1449 or PTO/5</li> </ul>		s)/Mail Date nformal Patent Application (PTO-152)	
Paper No(s)/Mail Date <u>5/21/04</u> .	6)  Other:		

Application/Control Number: 10/790,366

Art Unit: 2813

This is in response to the election filed 9/15/05.

## **DETAILED ACTION**

## Election/Restrictions

- 1. Claims 10-20 are withdrawn from further consideration pursuant to 37 CFR 1.142(b), as being drawn to a nonelected invention, there being no allowable generic or linking claim. Applicant timely traversed the restriction (election) requirement in the paper filed 9/15/05.
- 2. Applicant's election with traverse of claims 1-9 in the paper filed 9/15/05 is acknowledged. The traversal is on the ground(s) that no grounds were recited. This is not found persuasive because no grounds were recited.

The requirement is still deemed proper and is therefore made FINAL.

## Claim Rejections - 35 USC § 102

3. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 4. Claims 1-9 are rejected under 35 U.S.C. 102(b) as being anticipated by Tan (US006001706).

Tan teaches all of the positive steps of claims 1-9 as follows.

Art Unit: 2813

Regarding claim 1, Tan teaches a semiconductor substrate (10), a polish stop layer (13), a nitride containing layer (14) on the polish stop layer, forming a shallow trench (trench 1, layer 18) layer through a portion of the nitride containing layer, a portion of the polish stop layer, and a portion of the semiconductor substrate (figure 8A), removing the nitride containing layer by CMP (column 5 lines 53-57), and planarizing the shallow trench layer and the polish stop layer until the surfaces are co-planar (column 5 lines 53-57 and figure 10B).

Regarding claim 2, a barrier layer (12) is formed over the substrate.

Regarding claim 3, an aperture is etched through the nitride containing layer to expose a portion of the polish stop layer (column 4 lines 50-67, the multilayer (14,13, and 12 are etched. An opening (aperture) must be made in a portion of the nitride layer in order to etch an opening in the polish stop layer).

Regarding claim 4, a trench (1) is formed through the polish stop layer and the substrate and oxide (18) is deposited to form the layer (column 5 lines 47-49).

Regarding claim 5, the polish stop layer is polysilicon (column 4 line 27).

Regarding claim 6, the polish stop layer is polysilicon (column 4 line 27).

Regarding claim 7, the polish stop layer (13) is oxidized to form a field oxide (16' figure 8A).

Regarding claim 8, the nitride layer is Si3N4 column 4 lines 41-42).

Regarding claim 9, a liner (16) is formed between the semiconductor substrate and the shallow trench layer.

5. Any inquiry concerning this communication or earlier communications from the examiner should be directed to David S. Blum whose telephone number is (571)-272-1687) and e-mail address is <a href="mailto:David.blum@USPTO.gov">David.blum@USPTO.gov</a>.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Carl Whitehead Jr., can be reached at (571)-272-1702. Our facsimile number all patent correspondence to be entered into an application is (571) 273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

David S. Blum

December 12, 2005